



Bipolar NPN Bare Die – BTN6099

Part Description

The BTN6099 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6099.

Key Parameters:

- VCBO = 150V
- VCEO = 60V
- VEBO = 6V
- hFE = 120-300 @ VCE = 1V, IC = 2A
- VCE(Sat) = 0.55V @ IC = 6A, IB = 300mA
- fT = 150 MHz @ VCE = 10V, IE = 0A
- COBO = 50pF @ VCB = 10V

Features

Low VCE(sat) Designed to provide performance equivalent to ZETEX / DIODES INC. FZT851

Die Size (Unawn)

1670 μ m X 1670 μ m, 66 Mils X 66 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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